## Pattern forming method and apparatus for fabricating semiconductor device

Publication number: TW490736B

**Publication date:** 

2002-06-11

Inventor:

IRIE SHIGEO (JP)

**Applicant:** 

MATSUSHITA ELECTRIC IND CO LTD (JP)

Classification:

- international: G03F7/039; G03F7/16; G03F7/20; G03F7/26;

G03F7/36; G03F7/38; H01L21/027; G03F7/039;

G03F7/16; G03F7/20; G03F7/26; G03F7/36; G03F7/38;

H01L21/02; (IPC1-7): H01L21/027

- European:

G03F7/16Z; G03F7/26D; G03F7/38

Application number: TW20010111446 20010514 Priority number(s): JP20000192459 20000627

Also published as:

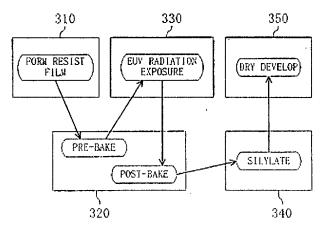
US6855485 (B2) US2001055731 (A1) KR20020001621 (A)

JP2002015971 (A)

Report a data error here

## Abstract of TW490736B

A resist film is formed out of a resist material on a substrate, and then pre-baked. Next, the prebaked resist film is exposed to extreme ultraviolet radiation through a photomask. Then, the exposed resist film is developed, thereby defining a resist pattern on the substrate. The pre-baking and exposing steps are carried out in a vacuum without subjecting the resist film to the air.



Data supplied from the esp@cenet database - Worldwide